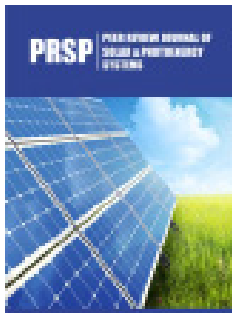


# Numerical Performance Analysis of an Environment Friendly High Efficiency Copper Based Perovskite Solar Cell Using SCAPS-1D Software

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## Abstract

In this research, we looked at the possibility of using hybrid organic-inorganic material  $(\text{CH}_3\text{NH}_3)_2\text{CuCl}_4$  as a material for the absorber in Perovskite Solar Cells (PSCs). Perovskite solar cells are becoming more popular as a possible boost to traditional photovoltaic cells' efficiency. The advantages of this cell over commercial silicon or other organic and inorganic solar cells are its high efficiency and eco-friendliness. In this study, we applied SCAPS-1D software to improve the device performance parameters, using ZnSe as the electron transport layer and  $\text{SrCu}_2\text{O}_2$ , which has been identified as a promising photovoltaic hole transport material in the  $(\text{CH}_3\text{NH}_3)_2\text{CuCl}_4$ -based Perovskite Solar Cell (PSC). To further enhance device performance, we have analyzed the effects of absorber and buffer layer thickness, acceptor density, absorber defect density and interfacial defect densities at the ETL/Absorber and Absorber/HTL interfaces. In addition, we also analyzed the effects of operating temperature, series resistance, and shunt resistance on the Quantum Efficiency (Q-E), back contact materials, current density-voltage (J-V) and overall optimum device performance. Gold is utilized for back contact. The efficient perovskite solar cell achieved an exceptionally high efficiency of 28.5% when the buffer layer was  $0.05\mu\text{m}$  thick and the Absorber layer was  $0.6\mu\text{m}$  thickness.

## Introduction

Scientists have been studying alternative energies for decades, since fossil fuels are dirty and finite. We will inevitably look for other energy sources. Fossil fuel sources are getting harder to come by. Consequently, the focus of scientific inquiry has shifted to sustainable energy, with solar energy continuing to be the primary source. Directly converting solar radiation into electrical power is harnessing solar energy [1,2]. The development of third-generation thin film Photo Voltaic (PV) technology has given rise to Perovskite Solar Cells (PSCs). Perovskite solar cells. Have mechanical, optical and physical characteristics that make them appropriate for photovoltaic systems. Scholars have examined some of these attributes through density functional theory and first-principles computation. [3-6]. Double or stacked perovskites are the most promising method for creating lead-free PSCs. This technique substitutes one monovalent  $\text{M}^+$  cation and one trivalent  $\text{M}^{2+}$  cation for the traditional two divalent Pb cations inside the perovskite structure. Consequently, these double perovskites have the following chemical structure:  $\text{A}_2\text{M}+\text{M}_2+\text{X}_6$ , where A can be  $\text{CH}(\text{NH}_2)$  or  $\text{CH}_3\text{NH}_{3+}$  [7]. With its creative structural design, ecologically friendly PSCs could be produced without sacrificing functionality, providing a more sustainable and clean method of solar energy harvesting. We used ZnSe as a buffer layer because ZnSe low cost, high optical transparency, which improves overall device efficiency [8]. With a broad 2.7eV bandgap, ZnSe is a significant technical optoelectronic semiconductor. ZnSe is a suitable replacement for solar photovoltaic cells. It is regarded as a crucial technical material because of its potential uses in various optical and electrical devices and as a buffer and window material for thin-film heterojunction solar cells [9]. This study used  $\text{SrCu}_2\text{O}_2$  as a buffer layer because oxides are more chemically stable

and less moisture sensitive than many organics or halide materials. Using SrCu<sub>2</sub>O<sub>2</sub> may improve device stability, particularly in operational/ambient exposure. For SCAPS modelling, this supports choosing buffer parameters with less drift (stable defect densities, lifetimes) and exploring stability under temperature variation [10]. It has been discovered that inorganic p-type transparent conductive oxides (TCOs), such as SrCu<sub>2</sub>O<sub>2</sub>, are excellent choices for a hole conductor in solar cells with suitable valence and conduction band locations [11-14]. The proposed perovskite solar cell used (CH<sub>3</sub>NH<sub>3</sub>)<sub>2</sub>CuCl<sub>4</sub> as an absorber layer for Lead-free, lower toxicity, replacing Pb with Cu makes (CH<sub>3</sub>NH<sub>3</sub>)<sub>2</sub>CuCl<sub>4</sub> an attractive, environmentally friendlier absorber for lead-free perovskite device concepts, which is an important design consideration in simulation studies where you want to explore non-toxic alternatives [15]. And also used ITO as an ETL layer because it has a realistic bandgap of ITO (~3.5-4.0 eV), so it doesn't absorb visible light significantly [16]. In this simulation, we introduce an ITO/ZnSe/ (CH<sub>3</sub>NH<sub>3</sub>)<sub>2</sub>CuCl<sub>4</sub> / SrCu<sub>2</sub>O<sub>2</sub>/Au perovskite solar cell. During this simulation, a total efficiency of 28.5% was gained. This perovskite solar cell can be used for its high efficiency.

**Numerical Simulation and Parameters of Materials**

The computational model's framework enables an understanding of the fundamentals of solar cells and the key parameters influencing their performance. Crucial one-dimensional semiconductor equations can be solved directly through the SCAPS-1D software [17]. The continuity equations for electrons and holes are as follows:

$$-\left(\frac{1}{q}\right) \frac{d j_n}{d X} - U_n + G = \frac{d n}{d t} \quad (1)$$

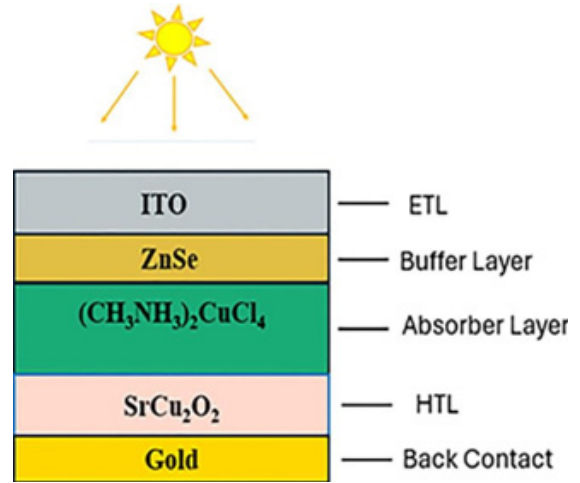
$$-\left(\frac{1}{q}\right) \frac{d j_p}{d X} - U_p + G = \frac{d p}{d t} \quad (2)$$

Where J<sub>n</sub> and j<sub>p</sub> are electrons and hole current densities and G is the generation rate. The Poisson equation is

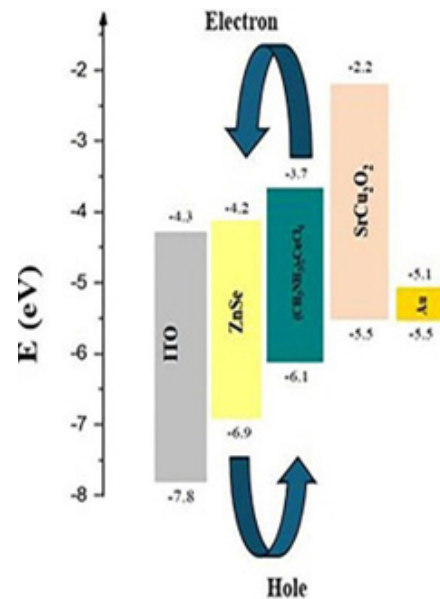
$$\frac{d^2}{d x^2} T(X) = \frac{e}{\epsilon_0 \epsilon_r} (\rho(X) + N_D - N_A + \rho_p - \rho_n) \quad (3)$$

The electrostatic potential is represented by ψ, the electrical charge is represented by e, the relative and vacuum permittivity by ε<sub>r</sub> and ε<sub>0</sub>, the concentrations of holes and electrons are represented by p and n, respectively, the charge impurities of the acceptor and donor types are represented by N<sub>A</sub> and N<sub>D</sub>, and the distributions of holes and electrons are represented by ρ<sub>p</sub> and ρ<sub>n</sub> [18]. The

literature and the user manual for SCAPS, a very potent program for solar cell performance, provide descriptions of the program and the algorithms it employs [19-22]. For this (CH<sub>3</sub>NH<sub>3</sub>)<sub>2</sub>CuCl<sub>4</sub> based Perovskite solar cell Figure 1 displays the schematic diagram (Figure 2) (Table 1).



**Figure 1:** Schematic diagram of proposed perovskite solar cell's schematic diagram.



**Figure 2:** Energy band alignment for various materials utilized in proposed Perovskite solar cell structure.

**Table 1:** For simulation the materials parameters used in proposed solar cell simulation.

Material Parameter	ITO [41]	ZnSe [9]	(CH <sub>3</sub> NH <sub>3</sub> ) <sub>2</sub> CuCl <sub>4</sub> [15]	SrCu <sub>2</sub> O <sub>2</sub> [10]
Thickness (μm)	0.1	0.05	0.6	0.2
Band gap (eV)	3.5	2.9	1.2	3.3
Electron affinity (eV)	4	4.1	4.17	2.2
Dielectric permittivity (relative)	9	10	10	9.7
CB effective Density (cm <sup>-3</sup> )	2.2x10 <sup>18</sup>	1.5 x10 <sup>18</sup>	2 x10 <sup>18</sup>	2 x10 <sup>20</sup>
VB effective Density (cm <sup>-3</sup> )	1.8 x10 <sup>19</sup>	1.8 x10 <sup>19</sup>	1.8 x10 <sup>18</sup>	2 x10 <sup>21</sup>
Electron thermal velocity (cm/s)	10 <sup>7</sup>	10 <sup>7</sup>	10 <sup>7</sup>	10 <sup>7</sup>

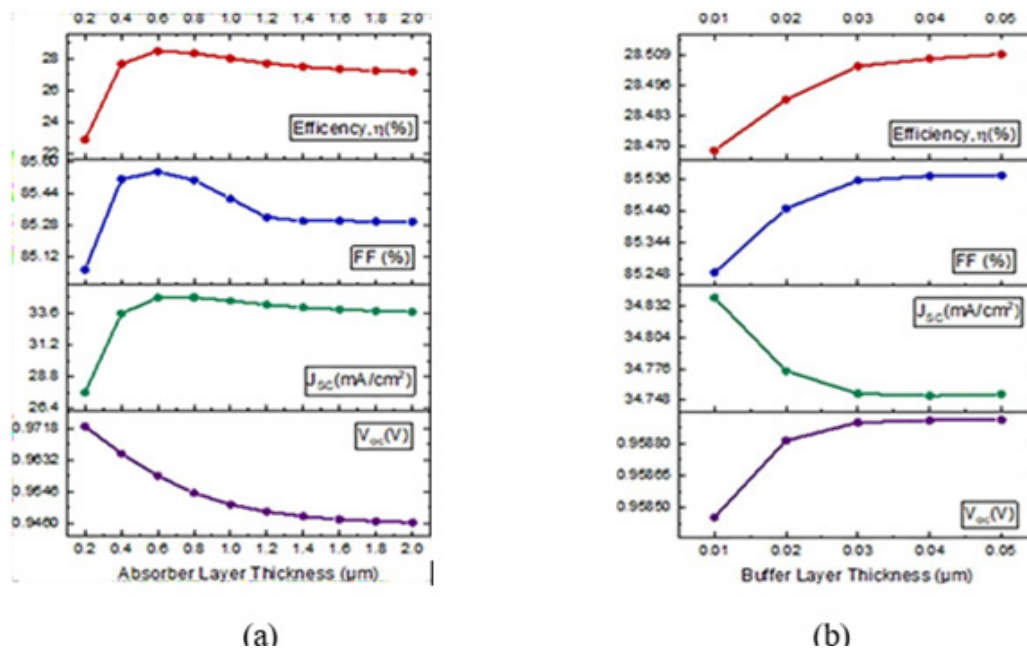
Hole thermal velocity (cm/s)	$10^7$	$10^7$	$10^7$	$10^7$
Electron mobility ( $\text{cm}^2/\text{V}\cdot\text{s}$ )	20	50	3	0.1
Hole mobility ( $\text{cm}^2/\text{V}\cdot\text{s}$ )	100	20	1	0.46
Donor density $N_D$ ( $\text{cm}^{-3}$ )	$1 \times 10^{21}$	$1 \times 10^{18}$	0	0
Acceptor density $N_A$ ( $\text{cm}^{-3}$ )	0	0	$1 \times 10^{18}$	$1 \times 10^{17}$
Total Defect Density ( $\text{cm}^{-3}$ )	$1 \times 10^{14}$	$1 \times 10^{13}$	$1 \times 10^{15}$	$1 \times 10^{15}$

## Results and Discussions

### Effect of absorber layer thickness & buffer layer thickness

The thickness of the absorber layer is a significant factor in establishing the device's specifications. The absorber layer thickness on the Perovskite Solar Cell (PSC) is depicted in Figure 3a. The thickness of the absorber layer varies from  $0.2\mu\text{m}$  to  $2\mu\text{m}$ . Figure 3a shows that all solar cell performance parameters, such as Open Circuit Voltage ( $V_{oc}$ ), Short Circuit Current ( $J_{sc}$ ), Fill Factor (FF) and efficiency, have improved. Efficiency increases from 22.8% to 28.5%,  $J_{sc}$  from  $24.62 \text{ mA}/\text{cm}^2$  to  $34.76 \text{ mA}/\text{cm}^2$ , and FF from 85.05% to 85.5%. From  $0.97\text{V}$  to  $0.94\text{V}$ ,  $V_{oc}$  falls. Because

of enhanced light absorption, Power Conversion Efficiency (PCE) rises from 22.8% to 28.5%. By making the material thicker, the absorber layer improves light absorption and carrier production, which raises the short-circuit current density [23]. Figure 3b shows the Electron Transport Layer (ETL) layer effect on the perovskite solar cell. ETL varies from  $0.01\mu\text{m}$  to  $0.05\mu\text{m}$ . It shows that all the parameters are slightly increased but almost constant. The change is negligible; for this simulation,  $0.05\mu\text{m}$  was gained as the optimized ETL thickness, where Open Circuit Voltage ( $V_{oc}$ )  $0.95\text{V}$ , Short Circuit Current ( $J_{sc}$ )  $34.75 \text{ mA}/\text{cm}^2$ , Fill Factor (FF) 85.54%, and efficiency 28.5% were achieved. This suggests that there is not much impact of ETL thickness on the perovskite solar cells (PSC's) electrical properties [24].

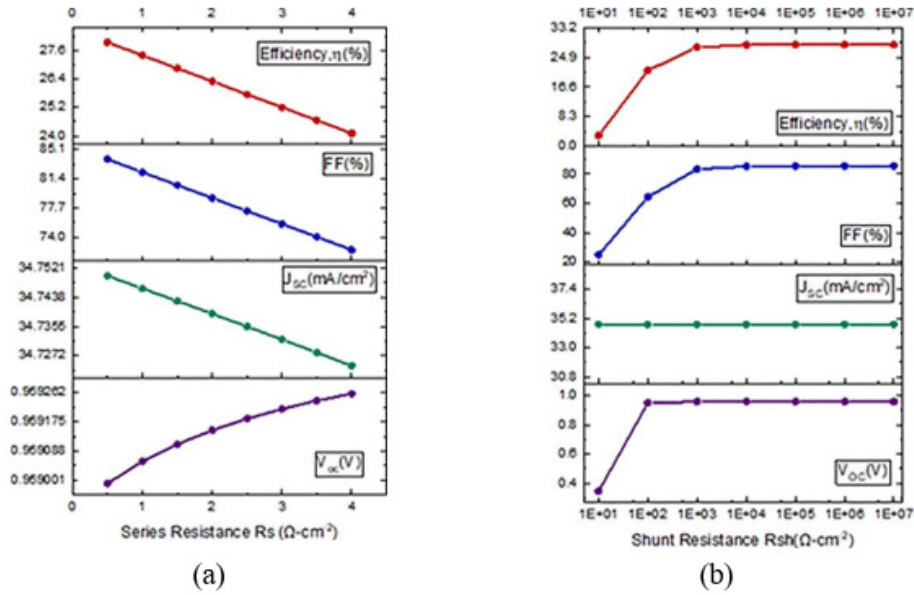


**Figure 3:** Effect of (a) Absorber Layer Thickness & (b) Buffer Layer Thickness on the solar cell parameters.

### Effect of Series & Shunt Resistance

Figure 4a & 4b illustrates how series and shunt resistance affect the solar cell. The series resistance is changed in Figure 4a from  $0.5\Omega\text{cm}^{-2}$  to  $4\Omega\text{cm}^{-2}$ . It has been noted that, apart from  $J_{sc}$ , all solar

cell properties decrease as series resistance rises. Fill Factor (FF) diminishes as the series resistance increases. At greater resistance values, the short circuit current decreases [25]. Here, equations 4 and 5 illustrate how series resistance affects the performance metrics.



**Figure 4:** Effect of (a) Series Resistance & (b) Shunt Resistance on the solar cell parameters.

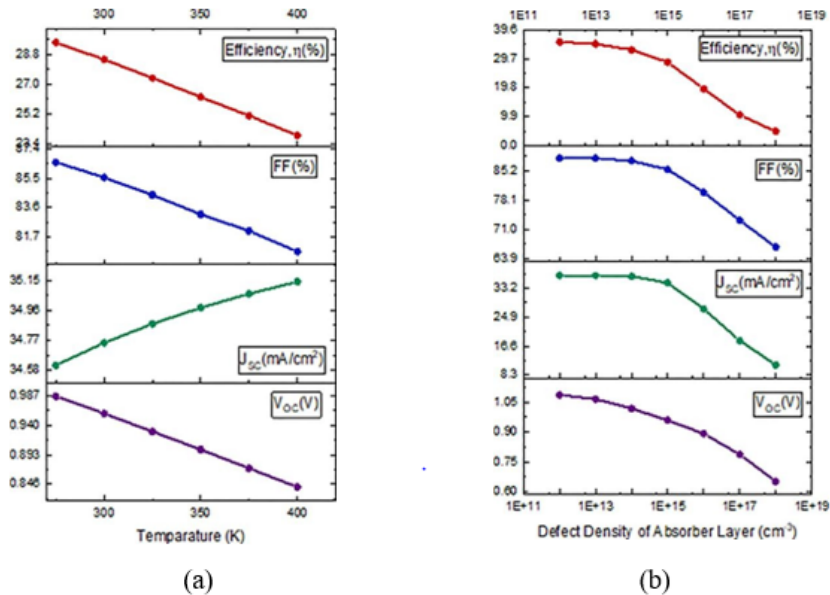
$$I_{SC} = I_0 \frac{70cg}{(e^{nkT-1})} \quad (4)$$

$$I_{SC} = I_l - I_o \frac{70cg}{(e^{nkT-1})} - \frac{v_{oc} + I_{sc}R_s}{\gamma sh} \quad (5)$$

where  $I_{sh}$  stands for shunt resistance and  $I_l$  for light-induced current. The math above makes it clear that when  $R_s$  rises, the Short

Circuit Current ( $I_{SC}$ ) value falls [26,27]. Figure 4b demonstrates the effect of shunt resistance on the proposed Perovskite Solar Cell (PSC). The shunt resistance is varied from  $1\text{E}1\Omega\text{cm}^{-2}$  to  $1\text{E}7\Omega\text{cm}^{-2}$ . As it's seen all the parameters are improved with variation. It's noticeable that there isn't much effect on short circuit current. Shunt resistance losses predominantly originate from defect state recombination; hence higher shunt resistance indicates fewer defect states [28].

### Effect of Temperature & Defect Density



**Figure 5:** Effect of (a) Temperature & (b) Defect density of Absorber Layer on the solar cell parameters.

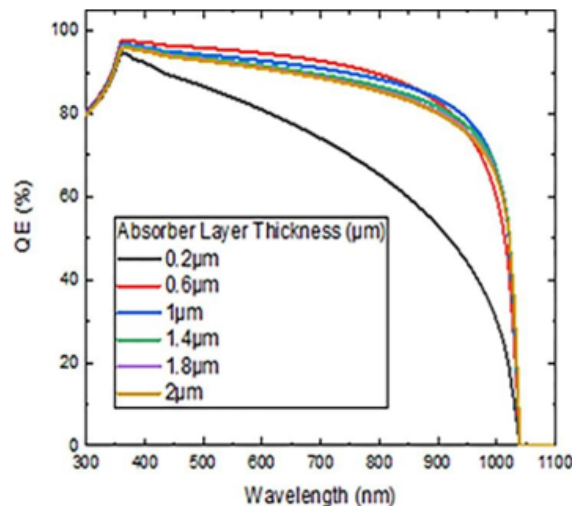
Figure 5a shows the temperature effect on the solar cell, where the temperature was adjusted from 275K to 400K. All the metrics except for short circuit current are seen to decrease

gradually. This may result from a decline in efficiency brought on by the defect density in the layers rising with temperature. Temperature-related increases in deformation stress may result

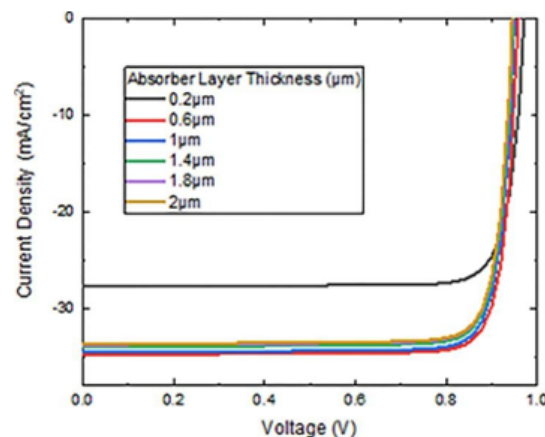
in a drop in the device's efficiency [29]. Here, Open Circuit Voltage ( $V_{oc}$ ) decreases from 0.987V to 0.83V, Fill Factor (FF) 86.5% to 80.2%, and Power Conversion Efficiency (PCE) 29.3% to 23%. Because temperature alters the diffusion length, which raises the series resistance, the device's FF and efficiency are reduced [30]. For this device simulation, an optimized temperature was gained at 300K. The impact of absorber layer defect density on the solar cell is depicted in Figure 5b. In this case, the defect varies between  $1E12cm^{-3}$  and  $1E18cm^{-3}$ . This variation affects every parameter in this case. Power Conversion Efficiency (PCE) decreases to 5% from 36%. Short Circuit Current ( $J_{sc}$ ) ranges from  $35.6mA/cm^2$  to  $11mA/cm^2$ , Fill Factor (FF) from 87.6% to 65%, and Open Circuit Voltage ( $V_{oc}$ ) from 1.1V to 0.62V. An increase in defect density causes shorter carrier lifetimes because more recombination and traps are present, making paths accessible. This lowers effective carrier mobility [31]. Defects must occur in all materials due to the possibility of achieving high efficiency at low defect concentrations [32]. For this reason, we selected the absorber layer defect density of  $1E15cm^{-3}$ .

## Quantum Efficiency & Current Density- Voltage Characteristics

Figure 6a shows the Quantum Efficiency (Q-E) vs wavelength characteristics curve. It shows the highest absorption in the wavelength range that is visible. There is a noticeable decline in Q-E in the infrared wavelength range. In this case, the absorber layer varies between 0.2 and  $2\mu m$ . An optimal thickness of  $0.6\mu m$  was obtained for this simulation. Figure 6a shows that as the thickness of the absorber layer increases, quantum efficiency rises at longer wavelengths. This is because there aren't enough photons inside the absorber layer to create enough electron-hole pairs [33]. Figure 6b displays the solar cell's J-V properties. In this simulation, the thickness of the absorber layer is adjusted from  $0.2\mu m$  to  $2\mu m$ . Here,  $0.6\mu m$  was the ideal thickness for the absorber layer, resulting in an Open Circuit Voltage ( $V_{oc}$ ) of 0.95V, Short Circuit Current ( $J_{sc}$ ) of  $34.75mA/cm^2$ , Fill Factor (FF) of 85.54%, and efficiency of 28.5%. When the absorber is thickened, the electron-hole pair is added, which raises the voltage and current [34].



(a)



(b)

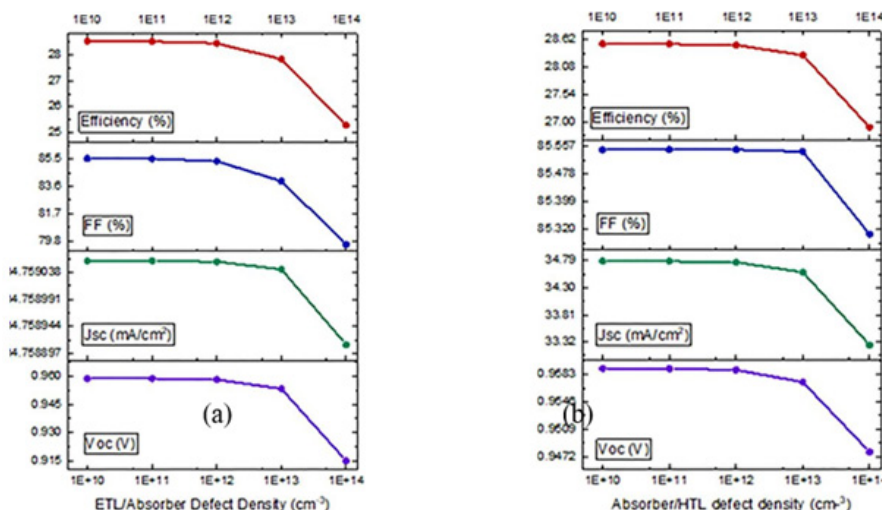
**Figure 6:** (a) Quantum Efficiency & (b) Current-Voltage characteristics of the PSC solar cell.

## Interface Defect

### Effect of ETL/ absorber and absorber/ HTL interface defect density

The impact of interface defect density on the suggested perovskite solar cell is depicted in Figure 7. This simulation changes the Electron Transport Layer (ETL/Absorber layer and the Absorber/ Hole Transport Layer (HTL) interface from  $1E10\text{cm}^{-3}$  to  $1E14\text{cm}^{-3}$ . Through simulation, it is found that interface fault densities significantly impact all the parameters. Low photocurrent

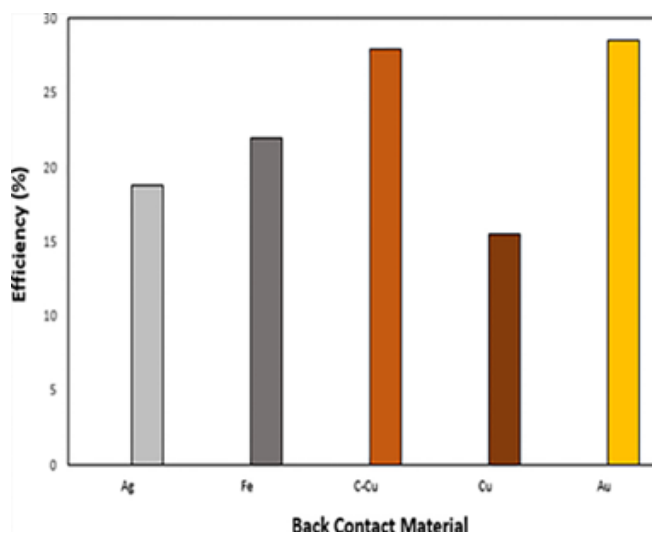
generation and overall efficiency are caused by high defect density because it creates mid-gap trap states that serve as recombination without radiation focal points, restricting diffusion length and carrier lifetime [35]. Figure 7b shows the Absorber/ Hole Transport Layer (HTL) defect density on the proposed perovskite solar cell. High interface fault density causes efficiency to drop quickly. Defect causes recombination centers for charging carriers, which lowers efficiency and current density [36]. Because of this, an interface defect density of less than  $1E11\text{cm}^{-3}$  [37] and a thickness of  $0.6\mu\text{m}$  are required for the maximum efficiency (Table 2).



**Figure 7:** Effect of (a) ETL/Absorber (b) Absorber/ HTL defect density on the solar cell parameters.

**Table 2:** Table-2 shows the interface defect density for the device.

Interface Defect Parameters	Defect Type	ETL/Absorber Neutral	HTL/Absorber Neutral
Capture cross section electrons ( $\text{cm}^2$ )		$1.00E-19$	$1.00E-19$
Capture cross section holes ( $\text{cm}^2$ )		$1.00E-19$	$1.00E-19$
Energetic distribution		Single	Single
Reference for defect energy level Et		Above the highest EV	Above the highest EV
Energy with respect to Reference (eV)		0.6	0.6
Total density (integrated over all energies) ( $\text{cm}^{-2}$ )		$1E10-1E14$	$1E10-1E14$



**Figure 8:** Different back contact materials' effects on solar cells.

**Table 3:** Table-3 shows metal work function for different materials.

Back Contact Metal	Ag	Fe	Au	Cu	Cu doped C
Work Function	4.7	4.8	5.3	4.6	5

### Effect of Back Contact Material

The metal's quantity of energy is known as the work function or the number of photons necessary to eliminate a single electron from its surface [38]. Improved solar cell efficiencies have been associated with higher work function values [39,40]. Au and Pt are expensive metals frequently employed as back contact in solar cells (Table 3). In this work, simulations were conducted to find an appropriate, commercially accessible metal to serve as the back contact for the proposed device configuration. Figure 8 shows the impact of various materials used for back contact on the PCE [41]. The maximum efficiency that was reached in this instance was 28.5%.

### Conclusion

This research studies a noble perovskite structure as ITO/ZnSe/(CH<sub>3</sub>NH<sub>3</sub>)<sub>2</sub>CuCl<sub>4</sub>/SrCu<sub>2</sub>O<sub>2</sub>/Au using SCAPS 1D simulation software. This study analyzes the effect of absorber layer thickness, buffer layer thickness, defect density of absorber layer, series resistance and shunt resistance to get the optimized value. Furthermore, quantum efficiency and current density-voltage characteristics were investigated for the proposed perovskite solar cell. After simulation, the optimum value of absorber layer thickness 0.6μm, total defect density Nt 1E15cm<sup>-3</sup> was gained. It's observed that at 300K, the device performs at its highest level. After simulation of Voc 0.95V, Jsc 34.75mA/cm<sup>2</sup>, FF 85.54% and efficiency 28.5% were gained as optimized values. Overall, this proposed perovskite solar cell is observed as a high-efficiency, green and stable heterojunction cell.

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